

David J Smith

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

673
papers

16,625
citations

63
h-index

99
g-index

686
ext. papers

17,520
ext. citations

4.1
avg, IF

6.36
L-index

#	Paper	IF	Citations
673	Rapid Screening Method for β -Adrenergic Agonist Residues Incurred in Animal Urine Using Direct Analysis in Real-Time Mass Spectrometry. <i>ACS Food Science & Technology</i> , 2022 , 2, 195-205		0
672	Comprehensive, in operando, and correlative investigation of defects and their impact on device performance. <i>Journal of Semiconductors</i> , 2022 , 43, 041102	2.3	1
671	Synchrotron X-ray diffraction observation of phase transformation during annealing of Si processed by high-pressure torsion. <i>Philosophical Magazine Letters</i> , 2021 , 101, 223-231	1	3
670	β -Ga ₂ O ₃ on Si (001) grown by plasma-assisted MBE with β -Al ₂ O ₃ (111) buffer layer: Structural characterization. <i>AIP Advances</i> , 2021 , 11, 045209	1.5	3
669	Heterovalent semiconductor structures and devices grown by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 030803	2.9	5
668	Atomic-Resolution Structure Imaging of Misfit Dislocations at Heterovalent III-V/III-V Interfaces. <i>ACS Applied Electronic Materials</i> , 2021 , 3, 2573-2579	4	0
667	Interfacial intermixing and anti-phase boundaries in GaP/Si(0 0 1) heterostructures. <i>Journal of Crystal Growth</i> , 2021 , 562, 126059	1.6	0
666	Selective area regrowth and doping for vertical gallium nitride power devices: Materials challenges and recent progress. <i>Materials Today</i> , 2021 , 49, 296-296	21.8	6
665	Effect of substrate morphology on stress-tested GaN-on-GaN vertical p-n diodes. <i>Microscopy and Microanalysis</i> , 2021 , 27, 1760-1761	0.5	0
664	Electrospray Ionization Inlet Tandem Mass Spectrometry: A Hyphenated Method for the Sensitive Determination of Chemicals in Animal Tissues and Body Fluids. <i>Journal of the American Society for Mass Spectrometry</i> , 2021 , 32, 14-20	3.5	3
663	Impact of Individual Structural Defects in GaAs Solar Cells: A Correlative and In Operando Investigation of Signatures, Structures, and Effects. <i>Advanced Optical Materials</i> , 2021 , 9, 2001487	8.1	3
662	Characterization of As-Grown and Regrown GaN-on-GaN Structures for Vertical p-n Power Devices. <i>Journal of Electronic Materials</i> , 2021 , 50, 2637-2642	1.9	3
661	The role of one-dimensional magnetic nanoprecipitates on the magnetoresistance of soft magnetic alloys: Study of a melt-spun Cu ₇₀ alloy. <i>Materials Chemistry and Physics</i> , 2021 , 266, 124517	4.4	0
660	Deep-UV wavelength-selective photodetectors based on lateral transport in AlGaN/AlN quantum well and dot-in-well structures. <i>AIP Advances</i> , 2021 , 11, 085109	1.5	0
659	Evaluation of rapid and standard tandem mass spectrometric methods to analyse veterinary drugs and their metabolites in antemortem bodily fluids from food animals.. <i>Food Additives and Contaminants - Part A Chemistry, Analysis, Control, Exposure and Risk Assessment</i> , 2021 , 1-13	3.2	1
658	Approaches to Phase Imaging in the Electron Microscope. <i>Microscopy and Microanalysis</i> , 2020 , 26, 1546-1546	15.46	
657	A hyperspectral unmixing framework for energy-loss near-edge structure analysis. <i>Ultramicroscopy</i> , 2020 , 218, 113096	3.1	2

656	Effects of growth temperature on electrical properties of GaN/AlN based resonant tunneling diodes with peak current density up to 1.01 MA/cm ² . <i>AIP Advances</i> , 2020 , 10, 055307	1.5	5
655	Annealing Effects on the Band Alignment of ALD SiO ₂ on (In _x Ga _{1-x}) ₂ O ₃ for x = 0.25. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 045001	2	
654	Direct Observation of Large Atomic Polar Displacements in Epitaxial Barium Titanate Thin Films. <i>Advanced Materials Interfaces</i> , 2020 , 7, 2000555	4.6	4
653	Changes in band alignment during annealing at 600 °C of ALD Al ₂ O ₃ on (In _x Ga _{1-x}) ₂ O ₃ for x = 0.25. <i>Journal of Applied Physics</i> , 2020 , 127, 105701	2.5	3
652	Dependence of growth temperature on the electrical properties and microstructure of MBE-grown AlN/GaN resonant tunneling diodes on sapphire. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020 , 38, 032214	1.3	2
651	Investigation of polycrystalline Ga _x In _{1-x} P for potential use as a solar cell absorber with tunable bandgap. <i>Journal of Applied Physics</i> , 2020 , 127, 073102	2.5	2
650	Reverse Leakage Analysis for As-Grown and Regrown Vertical GaN-on-GaN Schottky Barrier Diodes. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 1-1	2.3	19
649	Layered two-dimensional selenides and tellurides grown by molecular beam epitaxy 2020 , 235-269		1
648	Strategies for Analyzing Noncommon-Atom Heterovalent Interfaces: The Case of CdTe-on-InSb. <i>Advanced Materials Interfaces</i> , 2020 , 7, 1901658	4.6	9
647	Structural breakdown in high power GaN-on-GaN p-n diode devices stressed to failure. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020 , 38, 063402	2.9	4
646	Atomic-resolution structure imaging of defects and interfaces in compound semiconductors. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2020 , 66, 100498	3.5	9
645	Dielectric breakdown in epitaxial BaTiO ₃ thin films. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020 , 38, 044007	1.3	1
644	Electrospray ionization rapid screening sans liquid chromatography column: A sensitive method for detection and quantification of chemicals in animal tissues and urine. <i>Rapid Communications in Mass Spectrometry</i> , 2020 , 34, e8876	2.2	4
643	Formation of metastable bc8 phase from crystalline Si _{0.5} Ge _{0.5} by high-pressure torsion. <i>Materials Characterization</i> , 2020 , 169, 110590	3.9	6
642	Characterization of Misfit Dislocations at Heterovalent II-VI/III-V Interfaces. <i>Microscopy and Microanalysis</i> , 2019 , 25, 2610-2611	0.5	
641	Characterization of Etched and Grown GaN-GaN Schottky Diodes. <i>Microscopy and Microanalysis</i> , 2019 , 25, 2240-2241	0.5	
640	Defects at the surface of Ga ₂ O ₃ produced by Ar plasma exposure. <i>APL Materials</i> , 2019 , 7, 061102	5.7	25
639	Detection and quantification of residues in sheep exposed to trace levels of dietary zilpaterol HCl. <i>Food Additives and Contaminants - Part A Chemistry, Analysis, Control, Exposure and Risk Assessment</i> , 2019 , 36, 1289-1301	3.2	10

638	Self-assembled Bismuth Selenide (BiSe) quantum dots grown by molecular beam epitaxy. <i>Scientific Reports</i> , 2019 , 9, 3370	4.9	18
637	Strain-dependence of ϵ in thin film barium strontium titanate. <i>AIP Advances</i> , 2019 , 9, 025312	1.5	3
636	Molecular beam epitaxial growth and structural properties of hetero-crystalline and heterovalent PbTe/CdTe/InSb structures. <i>Journal of Applied Physics</i> , 2019 , 126, 045708	2.5	3
635	Atomic Structure of Extended Defects in GaAs-based Heterostructures. <i>Microscopy and Microanalysis</i> , 2019 , 25, 2022-2023	0.5	
634	Growth Habits of Bismuth Selenide (Bi ₂ Se ₃) Layers and Nanowires over Stranski-Krastanov Indium Arsenide Quantum Dots. <i>Crystal Growth and Design</i> , 2019 , 19, 6989-6993	3.5	2
633	Electron Holography. <i>Springer Handbooks</i> , 2019 , 767-818	1.3	8
632	Quantitative measurement of nanoscale electrostatic potentials and charges using off-axis electron holography: Developments and opportunities. <i>Ultramicroscopy</i> , 2019 , 203, 105-118	3.1	12
631	Epitaxial Oxides on Glass: A Platform for Integrated Oxide Devices. <i>ACS Applied Nano Materials</i> , 2019 , 2, 7713-7718	5.6	4
630	Microstructural Characterization of Defects and Chemical Etching for HgCdSe/ZnTe/Si (211) Heterostructures. <i>Journal of Electronic Materials</i> , 2019 , 48, 571-582	1.9	2
629	Strain relaxation in low-mismatched GaAs/GaAs _{1-x} Sb _x /GaAs heterostructures. <i>Acta Materialia</i> , 2019 , 162, 103-115	8.4	10
628	Surface structure analysis of Eu Zintl template on Ge(001). <i>Surface Science</i> , 2018 , 674, 94-102	1.8	7
627	Development of an immunochromatographic assay for the β -adrenergic agonist feed additive zilpaterol. <i>Food Additives and Contaminants - Part A Chemistry, Analysis, Control, Exposure and Risk Assessment</i> , 2018 , 35, 1519-1529	3.2	6
626	Growth of II-VI/III-V heterovalent quantum structures. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 02D110	1.3	5
625	Crystalline SrZrO ₃ deposition on Ge (001) by atomic layer deposition for high-k dielectric applications. <i>Journal of Applied Physics</i> , 2018 , 124, 044102	2.5	9
624	Defect Evolution in GaAs-based Low-mismatch Heterostructures. <i>Microscopy and Microanalysis</i> , 2018 , 24, 6-7	0.5	
623	Atomic structure of dissociated 60° dislocations in GaAs/GaAs _{0.92} Sb _{0.08} /GaAs heterostructures. <i>Scripta Materialia</i> , 2018 , 153, 77-80	5.6	4
622	Correlative Characterization of Defect Clusters in GaAs Solar Cells by High-Resolution TEM and Spatially Resolved Optical Techniques. <i>Microscopy and Microanalysis</i> , 2018 , 24, 136-137	0.5	
621	Impact of metastable phases on electrical properties of Si with different doping concentrations after processing by high-pressure torsion. <i>Scripta Materialia</i> , 2018 , 157, 120-123	5.6	11

620	Effect of SrTiO ₃ oxygen vacancies on the conductivity of LaTiO ₃ /SrTiO ₃ heterostructures. <i>Journal of Applied Physics</i> , 2018 , 124, 185303	2.5	14
619	EuO epitaxy by oxygen scavenging on SrTiO ₃ (001): Effect of SrTiO ₃ thickness and temperature. <i>Journal of Applied Physics</i> , 2018 , 124, 235301	2.5	6
618	Investigation of defect creation in GaP/Si(0 0 1) epitaxial structures. <i>Journal of Crystal Growth</i> , 2018 , 503, 36-44	1.6	10
617	Atmospheric Solid Analysis Probe and Modified Desorption Electrospray Ionization Mass Spectrometry for Rapid Screening and Semi-Quantification of Zilpaterol in Urine and Tissues of Sheep. <i>Journal of Agricultural and Food Chemistry</i> , 2018 , 66, 10871-10880	5.7	12
616	An EELS signal-from-background separation algorithm for spectral line-scan/image quantification. <i>Ultramicroscopy</i> , 2018 , 195, 25-31	3.1	6
615	Large positive linear magnetoresistance in the two-dimensional t electron gas at the EuO/SrTiO interface. <i>Scientific Reports</i> , 2018 , 8, 7721	4.9	31
614	The scientific careers of Robert Sinclair and Nestor Zaluzec - A brief sketch. <i>Ultramicroscopy</i> , 2017 , 176, 2-4	3.1	
613	Zintl layer formation during perovskite atomic layer deposition on Ge (001). <i>Journal of Chemical Physics</i> , 2017 , 146, 052817	3.9	9
612	Structural evolution of dilute magnetic (Sn,Mn)Se films grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2017 , 121, 075301	2.5	5
611	Observation of compound semiconductors and heterovalent interfaces using aberration-corrected scanning transmission electron microscopy. <i>Journal of Materials Research</i> , 2017 , 32, 921-927	2.5	6
610	Surface preparation of freestanding GaN substrates for homoepitaxial GaN growth by rf-plasma MBE. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017 , 35, 02B109-3	1.3	19
609	High-resolution transmission electron microscopy analysis of bulk nanograined silicon processed by high-pressure torsion. <i>Materials Characterization</i> , 2017 , 129, 163-168	3.9	17
608	Correlation of Etch Pits and Dislocations in As-grown and Thermal Cycle-Annealed HgCdTe(211) Films. <i>Journal of Electronic Materials</i> , 2017 , 46, 5007-5019	1.9	5
607	Substrate-independent analysis of microcrystalline silicon thin films using UV Raman spectroscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1700204	1.3	4
606	Recent studies of oxide-semiconductor heterostructures using aberration-corrected scanning transmission electron microscopy. <i>Journal of Materials Research</i> , 2017 , 32, 912-920	2.5	7
605	Band offsets of epitaxial cubic boron nitride deposited on polycrystalline diamond via plasma-enhanced chemical vapor deposition. <i>Applied Physics Letters</i> , 2017 , 111, 171604	3.4	11
604	Microscale magnetic compasses. <i>Journal of Applied Physics</i> , 2017 , 122, 094301	2.5	
603	High-resolution transmission electron microscopy analysis of nanograined germanium produced by high-pressure torsion. <i>Materials Characterization</i> , 2017 , 132, 132-138	3.9	16

602	Characterization of Semiconductor Materials Using Electron Holography. <i>Microscopy and Microanalysis</i> , 2017 , 23, 1404-1405	0.5	
601	Epitaxial growth of barium titanate thin films on germanium via atomic layer deposition. <i>Journal of Crystal Growth</i> , 2017 , 476, 6-11	1.6	12
600	Thickness-Dependent Defect Evolution in GaAs _{0.92} Sb _{0.08} /GaAs Heterostructures. <i>Microscopy and Microanalysis</i> , 2017 , 23, 1482-1483	0.5	
599	Integration of ferroelectric BaTiO ₃ with Ge: The role of a SrTiO ₃ buffer layer investigated using aberration-corrected STEM. <i>Applied Physics Letters</i> , 2017 , 110, 252901	3.4	5
598	Above 400-K robust perpendicular ferromagnetic phase in a topological insulator. <i>Science Advances</i> , 2017 , 3, e1700307	14.3	96
597	ELNES spectrum unmixing and mapping for oxide/oxide interfaces.. <i>Microscopy and Microanalysis</i> , 2017 , 23, 1588-1589	0.5	
596	Aberration-corrected STEM Imaging and EELS Mapping of BaTiO ₃ /SrTiO ₃ Interfacial Defects. <i>Microscopy and Microanalysis</i> , 2017 , 23, 1598-1599	0.5	
595	AlGaIn/GaN High Electron Mobility Transistor Grown and Fabricated on ZrTi Metallic Alloy Buffer Layers. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, S3078-S3080	2	1
594	Correlation of Etch Pits and Dislocations in As-grown and Thermal-Cycle-Annealed HgCdTe(211) Films. <i>Microscopy and Microanalysis</i> , 2017 , 23, 1526-1527	0.5	
593	Heterovalent ZnTe/GaSb and ZnSe/GaAs Grown by Molecular Beam Epitaxy. <i>Microscopy and Microanalysis</i> , 2017 , 23, 1472-1473	0.5	
592	Critical issues for homoepitaxial GaN growth by molecular beam epitaxy on hydride vapor-phase epitaxy-grown GaN substrates. <i>Journal of Crystal Growth</i> , 2016 , 456, 121-132	1.6	24
591	Characterization of structural defects in SnSe ₂ thin films grown by molecular beam epitaxy on GaAs (111)B substrates. <i>Journal of Crystal Growth</i> , 2016 , 453, 58-64	1.6	10
590	Contradictory nature of Co doping in ferroelectric BaTiO ₃ . <i>Physical Review B</i> , 2016 , 94,	3.3	7
589	Extraction of Quantitative Information from Non-optimum-focus Aberration-corrected HRTEM Images by Image Processing. <i>Microscopy and Microanalysis</i> , 2016 , 22, 932-933	0.5	1
588	Direct Mapping of Charge Distribution during Lithiation of Ge Nanowires Using Off-Axis Electron Holography. <i>Nano Letters</i> , 2016 , 16, 3748-53	11.5	31
587	Towards defect-free epitaxial CdTe and MgCdTe layers grown on InSb (001) substrates. <i>Journal of Crystal Growth</i> , 2016 , 439, 99-103	1.6	10
586	Screening and Confirmatory Analyses of Flunixin in Tissues and Bodily Fluids after Intravenous or Intramuscular Administration to Cull Dairy Cows with or without Lipopolysaccharide Challenge. <i>Journal of Agricultural and Food Chemistry</i> , 2016 , 64, 336-45	5.7	10
585	Thin Films of SnSe ₂ Grown by Molecular Beam Epitaxy on GaAs (111)B Substrates. <i>Microscopy and Microanalysis</i> , 2016 , 22, 1546-1547	0.5	1

584	ELNES analysis of $\text{BaTiO}_3/\text{SrTiO}_3$ and $\text{LaTiO}_3/\text{SrTiO}_3$ interfaces. <i>Microscopy and Microanalysis</i> , 2016 , 22, 1660-1661	0.5	
583	Characterization of electrical properties in axial Si-Ge nanowire heterojunctions using off-axis electron holography and atom-probe tomography. <i>Journal of Applied Physics</i> , 2016 , 120, 104301	2.5	9
582	Characterization of a ferroelectric $\text{BaTiO}_3/\text{SrTiO}_3$ heterostructure with interface-induced polarization. <i>Microscopy and Microanalysis</i> , 2016 , 22, 1508-1509	0.5	
581	Monolithic integration of perovskites on Ge(001) by atomic layer deposition: a case study with $\text{SrHf}_{1-x}\text{Ti}_x\text{O}_3$. <i>MRS Communications</i> , 2016 , 6, 125-132	2.7	13
580	Bright-field imaging of compound semiconductors using aberration-corrected scanning transmission electron microscopy. <i>Semiconductor Science and Technology</i> , 2016 , 31, 094002	1.8	7
579	Structural characterization of niobium oxide thin films grown on SrTiO_3 (111) and $(\text{La,Sr})(\text{Al,Ta})\text{O}_3$ (111) substrates. <i>Journal of Applied Physics</i> , 2016 , 120, 245302	2.5	10
578	Evaluation of AlGaIn/GaN high electron mobility transistors grown on ZrTi buffer layers with sapphire substrates. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 051208	1.3	4
577	Continuous control of spin polarization using a magnetic field. <i>Applied Physics Letters</i> , 2016 , 108, 212401	3.4	1
576	Evaluation of antimony segregation in InAs/InAs $_{1-x}$ Sb $_x$ type-II superlattices grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2016 , 119, 095702	2.5	35
575	Investigation of dilute-nitride alloys of GaAs $_x$ N $_y$ (0.01 $\leq x, y \leq 1$). <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 011210	1.3	5
574	Anti-phase boundaries at the $\text{SrTiO}_3/\text{Si}(001)$ interface studied using aberration-corrected scanning transmission electron microscopy. <i>Applied Physics Letters</i> , 2016 , 108, 091605	3.4	15
573	Spectral identification scheme for epitaxially grown single-phase niobium dioxide. <i>Journal of Applied Physics</i> , 2016 , 119, 095308	2.5	7
572	Morphological and microstructural stability of N-polar InAlN thin films grown on free-standing GaN substrates by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016 , 34, 021512	2.9	1
571	Spectrum and phase mapping across the epitaxial $\text{Al}_2\text{O}_3/\text{SrTiO}_3$ interface. <i>Applied Physics Letters</i> , 2016 , 108, 051606	3.4	7
570	Effect of indium in $\text{Al}_{0.65}\text{Ga}_{0.35}\text{N}/\text{Al}_{0.8}\text{Ga}_{0.2}\text{N}$ MQWs for the development of deep-UV laser structures in the form of graded-index separate confinement heterostructure (GRIN-SCH). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 1165-1169	1.6	15
569	Impact of dynamical scattering on quantitative contrast for aberration-corrected transmission electron microscope images. <i>Micron</i> , 2016 , 89, 77-86	2.3	2
568	Defect creation in InGaAs/GaAs multiple quantum wells: Structural properties. <i>Journal of Crystal Growth</i> , 2015 , 425, 43-48	1.6	5
567	Domain structure and perpendicular magnetic anisotropy in CoFe/Pd multilayers using off-axis electron holography. <i>Journal of Magnetism and Magnetic Materials</i> , 2015 , 388, 16-21	2.8	5

566	MBE growth of sharp interfaces in dilute-nitride quantum wells with improved nitrogen-plasma design. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 031209	1.3	8
565	Quasi-two-dimensional electron gas at the epitaxial alumina/SrTiO ₃ interface: Control of oxygen vacancies. <i>Journal of Applied Physics</i> , 2015 , 117, 095303	2.5	34
564	Recovery in dc and rf performance of off-state step-stressed AlGa _N /Ga _N high electron mobility transistors with thermal annealing. <i>Applied Physics Letters</i> , 2015 , 106, 153504	3.4	2
563	Plastic Deformation of BaTiO ₃ Ceramics by High-pressure Torsion and Changes in Phase Transformations, Optical and Dielectric Properties. <i>Materials Research Letters</i> , 2015 , 3, 216-221	7.4	52
562	Investigation of MBE-grown InAs _{1-x} Bi alloys and Bi-mediated type-II superlattices by transmission electron microscopy. <i>Journal of Crystal Growth</i> , 2015 , 425, 250-254	1.6	19
561	Investigation of single-layer/multilayer self-assembled InAs quantum dots on GaAs _{1-x} Sb _x /GaAs composite substrates. <i>Journal of Applied Physics</i> , 2015 , 118, 094303	2.5	4
560	Effect of interfacial oxygen on the microstructure of MBE-grown homoepitaxial N-polar Ga _N . <i>Journal of Crystal Growth</i> , 2015 , 409, 14-17	1.6	12
559	Determination of Mean Inner Potential and Inelastic Mean Free Path of ZnTe Using Off-Axis Electron Holography and Dynamical Effects Affecting Phase Determination. <i>Microscopy and Microanalysis</i> , 2015 , 21, 1406-1412	0.5	6
558	Charge control in N-polar InAlN high-electron-mobility transistors grown by plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 061207	1.3	10
557	Quasi-two-dimensional electron gas at the interface of Al ₂ O ₃ /SrTiO ₃ heterostructures grown by atomic layer deposition. <i>Journal of Applied Physics</i> , 2015 , 118, 115303	2.5	22
556	High Resolution TEM Observation of Nanocrystalline Silicon Fabricated by High Pressure Torsion (HPT). <i>Microscopy and Microanalysis</i> , 2015 , 21, 1783-1784	0.5	
555	Characterization of Two-Dimensional Electron Gas at the γ -Al ₂ O ₃ /SrTiO ₃ Interface. <i>Microscopy and Microanalysis</i> , 2015 , 21, 1309-1310	0.5	
554	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Bi ₂ Te ₃ by Multifunctionality of Native Defects. <i>Advanced Materials</i> , 2015 , 27, 3681-6	24	79
553	An indirect method of studying band alignments in nBn photodetectors using off-axis electron holography. <i>Applied Physics Letters</i> , 2015 , 107, 122109	3.4	4
552	Cross-Sectional Characterization of SrTiO ₃ /Si(001) Interfaces using Aberration-Corrected STEM. <i>Microscopy and Microanalysis</i> , 2015 , 21, 1305-1306	0.5	
551	Large-Collection-Angle BF STEM Imaging of Compound Semiconductors. <i>Microscopy and Microanalysis</i> , 2015 , 21, 1921-1922	0.5	1
550	Measurement of mean inner potential and inelastic mean free path of ZnO nanowires and nanosheet. <i>Materials Research Express</i> , 2015 , 2, 105003	1.7	3
549	Atomic layer deposition of crystalline SrHfO ₃ directly on Ge (001) for high-k dielectric applications. <i>Journal of Applied Physics</i> , 2015 , 117, 054101	2.5	39

548	Carrier density modulation in a germanium heterostructure by ferroelectric switching. <i>Nature Communications</i> , 2015 , 6, 6067	17.4	64
547	Atomic-scale chemical imaging and quantification of metallic alloy structures by energy-dispersive X-ray spectroscopy. <i>Scientific Reports</i> , 2014 , 4, 3945	4.9	57
546	Molecular beam epitaxy using bismuth as a constituent in InAs and a surfactant in InAs/InAsSb superlattices. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 02C120	1.3	23
545	Effect of proton irradiation on AlGaIn/GaN high electron mobility transistor off-state drain breakdown voltage. <i>Applied Physics Letters</i> , 2014 , 104, 082106	3.4	15
544	Enhancement of AlGaIn/GaN high electron mobility transistors off-state drain breakdown voltage via backside proton irradiation. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 021203	1.3	6
543	Characterization of a-plane GaN templates grown by HVPE and high efficiency deep UV emitting AlGaIn/AlN MQWs grown by MBE on such templates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 585-589		3
542	Nanostructure Property Control in AlPSi ₃ /Si(100) Semiconductors Using Direct Molecular Assembly: Theory Meets Experiment at the Atomic Level. <i>Chemistry of Materials</i> , 2014 , 26, 4092-4101	9.6	6
541	Optimization of In ₂ Se ₃ /Si(111) Heteroepitaxy To Enable Bi ₂ Se ₃ /In ₂ Se ₃ Bilayer Growth. <i>Crystal Growth and Design</i> , 2014 , 14, 4617-4623	3.5	5
540	Depletion of penicillin G residues in heavy sows after intramuscular injection. Part II: application of kidney inhibition swab tests. <i>Journal of Agricultural and Food Chemistry</i> , 2014 , 62, 7586-92	5.7	7
539	Fabrication of nanograined silicon by high-pressure torsion. <i>Journal of Materials Science</i> , 2014 , 49, 6565-6569	4.5	26
538	Epitaxy: A Chemical Route to Monolithic Integration of Crystalline Oxides on Semiconductors (Adv. Mater. Interfaces 8/2014). <i>Advanced Materials Interfaces</i> , 2014 , 1, n/a-n/a	4.6	1
537	Atomic Scale Studies of Structure and Bonding in AlPSi ₃ Alloys Grown Lattice-matched on Si(001). <i>Microscopy and Microanalysis</i> , 2014 , 20, 524-525	0.5	1
536	Improving the Spatial Resolution of Atomic-Scale EDS Mapping for Chemical Imaging and Quantification of Metallic Alloy Structures. <i>Microscopy and Microanalysis</i> , 2014 , 20, 130-131	0.5	
535	A Chemical Route to Monolithic Integration of Crystalline Oxides on Semiconductors. <i>Advanced Materials Interfaces</i> , 2014 , 1, 1400081	4.6	38
534	Epitaxial growth: Phenomenological model of defect creation 2014 ,		1
533	Band alignment of a HfO ₂ -VO ₂ -HfO ₂ confined well structure on silicon. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 011203	1.3	5
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